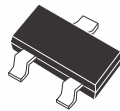


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**CMPT5086
CMPT5087**

PNP SILICON TRANSISTOR



SOT-23 CASE

Central Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT5086, CMPT5087 types are PNP silicon transistors manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring high gain and low noise.

Marking Codes are C2P and C2Q Respectively.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	3.0	V
Collector Current	I _C	50	mA
Power Dissipation	P _D	350	mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	357	°C/W

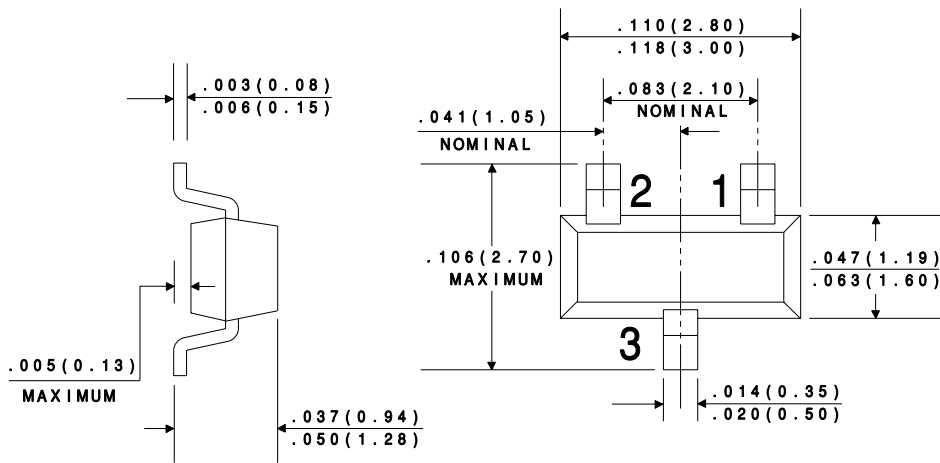
ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	CMPT5086		CMPT5087		UNITS
		MIN	MAX	MIN	MAX	
I _{CBO}	V _{CB} =10V		10		10	nA
I _{CBO}	V _{CB} =35V		50		50	nA
BV _{CB0}	I _C =100μA	50		50		V
BV _{CEO}	I _C =1.0mA	50		50		V
BV _{EBO}	I _E =100μA	3.0		3.0		V
V _{CE(SAT)}	I _C =10mA, I _B =1.0mA		0.30		0.30	V
V _{BE(SAT)}	I _C =10mA, I _B =1.0mA		0.85		0.85	V
h _{FE}	V _{CE} =5.0V, I _C =0.1mA	150	500	250	800	
h _{FE}	V _{CE} =5.0V, I _C =1.0mA	150		250		
h _{FE}	V _{CE} =5.0V, I _C =10mA	150		250		
f _T	V _{CE} =5.0V, I _C =500μA, f=20MHz	40		40		MHz
f _T	V _{CB} =5.0V, I _E =0, f=1.0MHz		4.0		4.0	pF
h _{fe}	V _{CE} =5.0V, I _C =1.0mA, f=1.0kHz	150	600	250	900	



SYMBOL	TEST CONDITIONS	CMPT5086		CMPT5087		UNITS
		MIN	MAX	MIN	MAX	
NF	$V_{CE}=5.0V$, $I_C=20mA$, $R_S=10k\Omega$ $f=10Hz$ to $15.7kHz$		3.0		2.0	dB
NF	$V_{CE}=5.0V$, $I_C=100\mu A$, $R_S=3.0k\Omega$, $f=1.0kHz$		3.0		2.0	dB

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR